



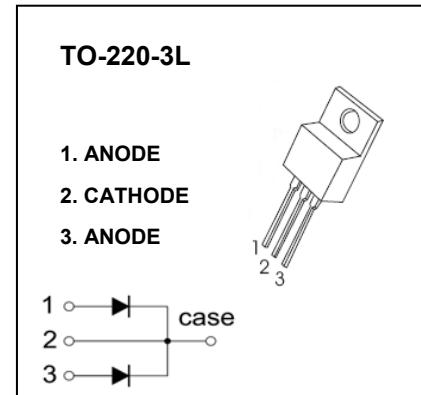
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220-3L Plastic-Encapsulate Diodes

MBR4045CT SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak repetitive reverse voltage	45	V
V_{RWM}	Working peak reverse voltage		
V_R	DC blocking voltage		
$V_{R(\text{RMS})}$	RMS reverse voltage	31.5	V
I_o	Average rectified output current	40	A
I_{FSM}	Non-Repetitive peak forward surge current 5μs sine wave	900	A
P_D	Power dissipation	2	W
$R_{\theta JA}$	Thermal resistance from junction to ambient	50	°C/W
T_j	Junction temperature	125	°C
T_{stg}	Storage temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=1\text{mA}$	45			V
Reverse current	I_R	$V_R=45\text{V}$			1	mA
Forward voltage	$V_{F(1)}$	$I_F=20\text{A}$			0.6	V
	$V_{F(2)}^*$	$I_F=40\text{A}$			0.78	
Typical total capacitance	C_{tot}	$V_R=5\text{V}, f=100\text{KHz to } 1\text{MHz}$		900		pF

*Pulse test